

**SCHOTTKY BARRIER DIODE**
**FEATURES**

- Low Forward Voltage Drop
- Guard Ring Die Construction for Transient Protection
- Ideal for low logic level applications
- Low Capacitance
- Also Available in Lead Free Version


**MARKING: SG**
**Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>A</sub>=25°C**

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V <sub>RM</sub>	30	V
Forward Current	I <sub>FM</sub>	100	mA
Forward surge Current    t <sub>p</sub> =10ms	I <sub>FSM</sub>	750	mA
Power dissipation        T <sub>C</sub> =25°C	P <sub>tot</sub>	250	mW
Thermal resistance junction to ambient air	T <sub>eJA</sub>	500	°C/W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>STG</sub>	-65~+150	°C

**Electrical Ratings @T<sub>A</sub>=25°C**

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Reverse breakdown voltage	V <sub>R</sub>	30			V	I <sub>R</sub> =100μA
Forward voltage	V <sub>F</sub>		300 360 470 580	550 800	mV	I <sub>F</sub> =2mA I <sub>F</sub> =15mA I <sub>F</sub> =50mA I <sub>F</sub> =100mA
Reverse current	I <sub>R</sub>			1	μA	V <sub>R</sub> =25V
Capacitance between terminals	C <sub>T</sub>		7		pF	V <sub>R</sub> =10V,f=1MHz

## Typical Characteristics

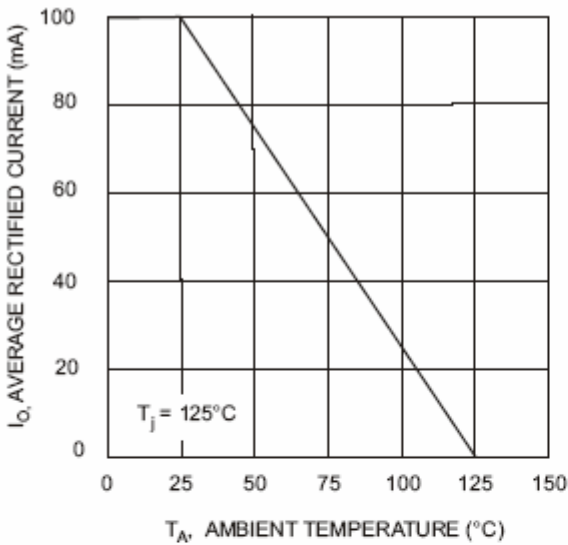


Fig. 1 Forward Current Derating Curve

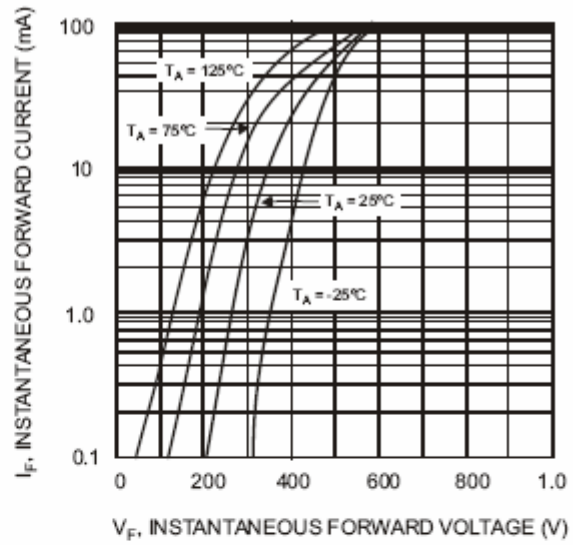


Fig. 2 Typical Forward Characteristics

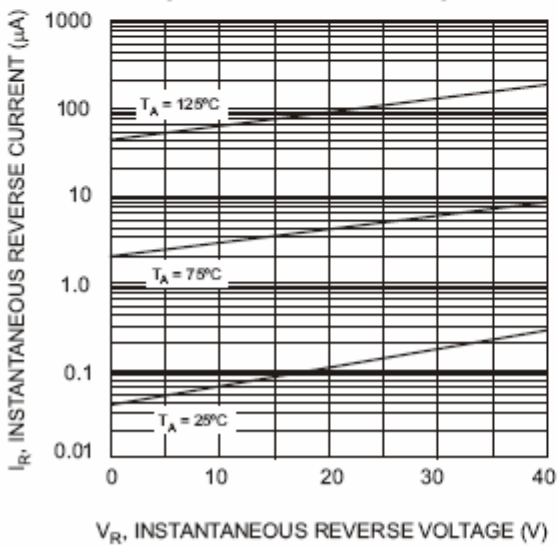


Fig. 3 Typical Reverse Characteristics

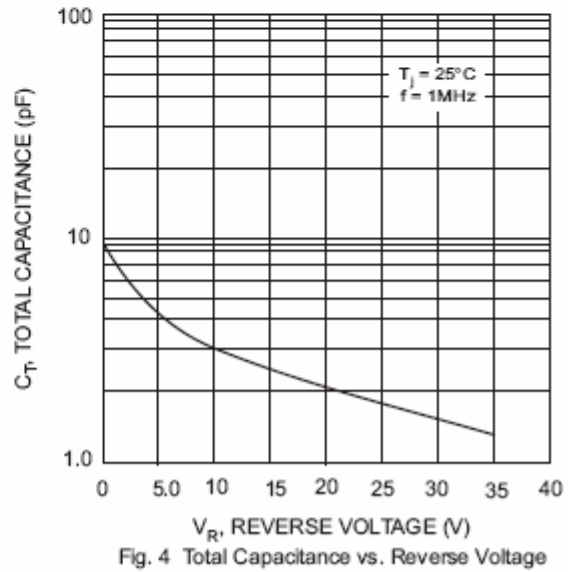


Fig. 4 Total Capacitance vs. Reverse Voltage